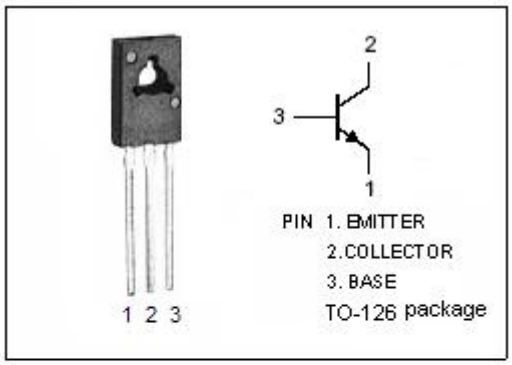
isc Silicon NPN Power Transistor — 2SC5694

DESCRIPTION

- High speed switching
- Large Current Capacity
- High allowable power dissipation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

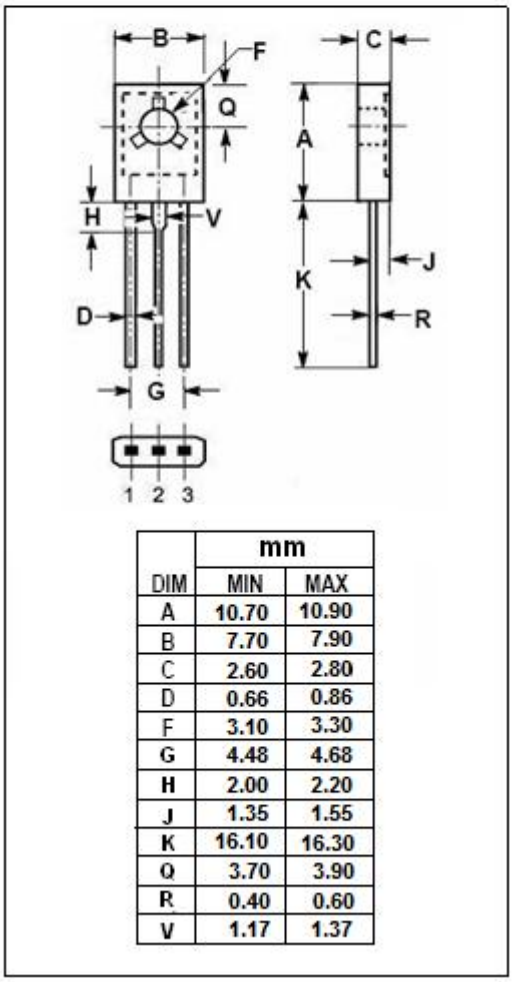


APPLICATIONS

- Relay drivers,lanp drivers,motor drivers and printer drivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ T_C=25℃	10	W
	Collector Power Dissipation @ T_a=25℃	1.2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.90
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	16.10	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 10μA; I_E= 0	60			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA; R_{BE}= ∞	50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= 10μA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 125mA			0.26	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=2.5A; I_B= 125mA			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}=2V	150		300	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V		330		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V, f_{test}= 1MHz		28		pF